

Approval Sheet

| | |
|-----------------------|---------------------------------|
| Customer | |
| Product Number | M4RI-8GS1A5SJ-C |
| Module speed | PC4-2400 |
| Pin | 288 pin |
| CI-tRCD-tRP | 17-17-17 |
| Operating Temp | -40°C~85°C |
| Date | 14th May 2021 |

**The Total Solution For
Industrial Flash Storage**

Rev 1.1

1. Features

Key Parameter

| Industry Nomenclature | Speed Grade | Data Rate MT/s | | | CL | tRCD | tRP |
|--------------------------|----------------|----------------|-------|-------|----|------|-----|
| | | CL=13 | CL=15 | CL=17 | | | |
| PC4-2400 | S | 1866 | 2133 | 2400 | 17 | 17 | 17 |

- JEDEC Standard 288-pin Registered Dual In-Line Memory Module
- Intend for PC4-2400 applications
- Inputs and Outputs are SSTL-12 compatible
- VDD=VDDQ= 1.2 Volt (1.14V~1.26V)
- VPP=2.5 Volt (2.375V~2.75V)
- VDDSPD=2.2-3.6V
- Low-Power auto self-refresh (LPASR)
- SDRAMs have 16 internal banks for concurrent operation (4 Bank Group of 4 banks each)
- Normal and Dynamic On-Die Termination for data, strobe and mask signals.
- Data bus inversion (DBI) for data bus
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the MRS
- Selectable BC4 or BL8 on-the fly (OTF)
- Gold Plating Thickness 30μ"
- Fly-By topology
- Terminated control, command and address bus
- Programmable /CAS Latency: 10,11,12,13,14,15,16,17,18
- On-die VREFDQ generation and Calibration
- Temperature Sensor with SPD EEPROM
- Support ECC function
- RoHS and Halogen free (*Section 11*)

2. Ordering Information

| DDR4 W/T RDIMM | | | | | | |
|------------------------|---------|----------|-------------------|----------------|----------------|-----|
| Part Number | Density | Speed | DIMM Organization | Number of DRAM | Number of rank | ECC |
| M4RI-8GS1A5SJ-C | 8GB | PC4-2400 | 1Gx72 | 9 | 1 | Y |

3. Pin Configurations (Front side/Back side)

| Pin | Front | Pin | Back | Pin | Front | Pin | Back | Pin | Front | Pin | Back | Pin | Front | Pin | Back |
|-----|----------------------|-----|--------|-----|-----------------------|-----|---------|-----|----------------------|-----|----------------|-----|----------------------|-----|--------|
| 1 | NC | 145 | NC | 37 | VSS | 181 | DQ29 | 73 | VDD | 217 | VDD | 109 | VSS | 253 | DQ41 |
| 2 | VSS | 146 | VREFCA | 38 | DQ24 | 182 | VSS | 74 | CK0_t | 218 | CK1_t | 110 | DQS14_t/ TDQS14_t | 254 | VSS |
| 3 | DQ4 | 147 | VSS | 39 | VSS | 183 | DQ25 | 75 | CK0_c | 219 | CK1_c | 111 | DQS14_c/ TDQS14_c | 255 | DQS5_c |
| 4 | VSS | 148 | DQ5 | 40 | DQS12_t/ TDQS12_t | 184 | VSS | 76 | VDD | 220 | VDD | 112 | VSS | 256 | DQS5_t |
| 5 | DQ0 | 149 | VSS | 41 | DQS12_c/ TDQS12_c | 185 | DQS3_c | 77 | VTT | 221 | VTT | 113 | DQ46 | 257 | VSS |
| 6 | VSS | 150 | DQ1 | 42 | VSS | 186 | DQS3_t | 78 | EVENT_n | 222 | PARITY | 114 | VSS | 258 | DQ47 |
| 7 | DQS9_t/ TDQS9_t | 151 | VSS | 43 | DQ30 | 187 | VSS | 79 | A0 | 223 | VDD | 115 | DQ42 | 259 | VSS |
| 8 | DQS09_c/ TDQS9_c | 152 | DQS0_c | 44 | VSS | 188 | DQ31 | 80 | VDD | 224 | BA1 | 116 | VSS | 260 | DQ43 |
| 9 | VSS | 153 | DQS0_t | 45 | DQ26 | 189 | VSS | 81 | BA0 | 225 | A10/AP | 117 | DQ52 | 261 | VSS |
| 10 | DQ6 | 154 | VSS | 46 | VSS | 190 | DQ27 | 82 | RAS_n /A16 | 226 | VDD | 118 | VSS | 262 | DQ53 |
| 11 | VSS | 155 | DQ7 | 47 | CB4 | 191 | VSS | 83 | VDD | 227 | RFU | 119 | DQ48 | 263 | VSS |
| 12 | DQ2 | 156 | VSS | 48 | VSS | 192 | CB5 | 84 | CS0_n | 228 | WE_n/ A14 | 120 | VSS | 264 | DQ49 |
| 13 | VSS | 157 | DQ3 | 49 | CB0 | 193 | VSS | 85 | VDD | 229 | VDD | 121 | DQS15_t/ TDQS15_t | 265 | VSS |
| 14 | DQ12 | 158 | VSS | 50 | VSS | 194 | CB1 | 86 | CAS_n/ A15 | 230 | NC | 122 | DQS15_c/ TDQS15_c | 266 | DQS6_c |
| 15 | VSS | 159 | DQ13 | 51 | TDQS17_t/ TDQS17_t | 195 | VSS | 87 | ODT0 | 231 | VDD | 123 | VSS | 267 | DQS6_t |
| 16 | DQ8 | 160 | VSS | 52 | DQS17_c/ TDQS17_c | 196 | DQS8_c | 88 | VDD | 232 | A13 | 124 | DQ54 | 268 | VSS |
| 17 | VSS | 161 | DQ9 | 53 | VSS | 197 | DQS8_t | 89 | CS1_n | 233 | VDD | 125 | VSS | 269 | DQ55 |
| 18 | DQS10_t/ TDQS10_t | 162 | VSS | 54 | CB6 | 198 | VSS | 90 | VDD | 234 | A17 | 126 | DQ50 | 270 | VSS |
| 19 | DQS10_c/ TDQS10_c | 163 | DQS1_c | 55 | VSS | 199 | CB7 | 91 | ODT1 | 235 | NC/C2 | 127 | VSS | 271 | DQ51 |
| 20 | VSS | 164 | DQS1_t | 56 | CB2 | 200 | VSS | 92 | VDD | 236 | VDD | 128 | DQ60 | 272 | VSS |
| 21 | DQ14 | 165 | VSS | 57 | VSS | 201 | CB3 | 93 | CS2_n/C0,NC | 237 | CS3_n C1,NC | 129 | VSS | 273 | DQ61 |
| 22 | VSS | 166 | DQ15 | 58 | RESET_n | 202 | VSS | 94 | VSS | 238 | SA2 | 130 | DQ56 | 274 | VSS |
| 23 | DQ10 | 167 | VSS | 59 | VDD | 203 | CKE1 | 95 | DQ36 | 239 | VSS | 131 | VSS | 275 | DQ57 |
| 24 | VSS | 168 | DQ11 | 60 | CKE0 | 204 | VDD | 96 | VSS | 240 | DQ37 | 132 | DQS16_t/ TDQS16_t | 276 | VSS |
| 25 | DQ20 | 169 | VSS | 61 | VDD | 205 | RFU | 97 | DQ32 | 241 | VSS | 133 | DQS16_c /TDQS16_c | 277 | DQS7_c |
| 26 | VSS | 170 | DQ21 | 62 | ACT_n | 206 | VDD | 98 | VSS | 242 | DQ33 | 134 | VSS | 278 | DQS7_t |
| 27 | DQ16 | 171 | VSS | 63 | BG0 | 207 | BG1 | 99 | DQS13_t/ TDQ13_t | 243 | VSS | 135 | DQ62 | 279 | VSS |
| 28 | VSS | 172 | DQ17 | 64 | VDD | 208 | ALERT_n | 100 | DQS13_c/ TDQS13_c | 244 | DQS4_c | 136 | VSS | 280 | DQ63 |
| 29 | DQS11_t/ TDQS11_t | 173 | VSS | 65 | A12/BC_n | 209 | VDD | 101 | VSS | 245 | DQS4_t | 137 | DQ58 | 281 | VSS |
| 30 | DQS11_c/ TDQS11_c | 174 | DQS2_c | 66 | A9 | 210 | A11 | 102 | DQ38 | 246 | VSS | 138 | VSS | 282 | DQ59 |
| 31 | VSS | 175 | DQS2_t | 67 | VDD | 211 | A7 | 103 | VSS | 247 | DQ39 | 139 | SA0 | 283 | VSS |
| 32 | DQ22 | 176 | VSS | 68 | A8 | 212 | VDD | 104 | DQ34 | 248 | VSS | 140 | SA1 | 284 | VDDSPD |
| 33 | VSS | 177 | DQ23 | 69 | A6 | 213 | A5 | 105 | VSS | 249 | DQ35 | 141 | SCL | 285 | SDA |
| 34 | DQ18 | 178 | VSS | 70 | VDD | 214 | A4 | 106 | DQ44 | 250 | VSS | 142 | VPP | 286 | VPP |
| 35 | VSS | 179 | DQ19 | 71 | A3 | 215 | VDD | 107 | VSS | 251 | DQ45 | 143 | VPP | 287 | VPP |
| 36 | DQ28 | 180 | VSS | 72 | A1 | 216 | A2 | 108 | DQ40 | 252 | VSS | 144 | RFU | 288 | VPP |

Note:
1. NC = No Connect, RFU = Reserved for Future Use
2. Address A17 is only valid for 16 Gb x4 based SDRAMs.
3. RAS_n is a multiplexed function with A16.
4. CAS_n is a multiplexed function with A15.
5. WE_n is a multiplexed function with A14.

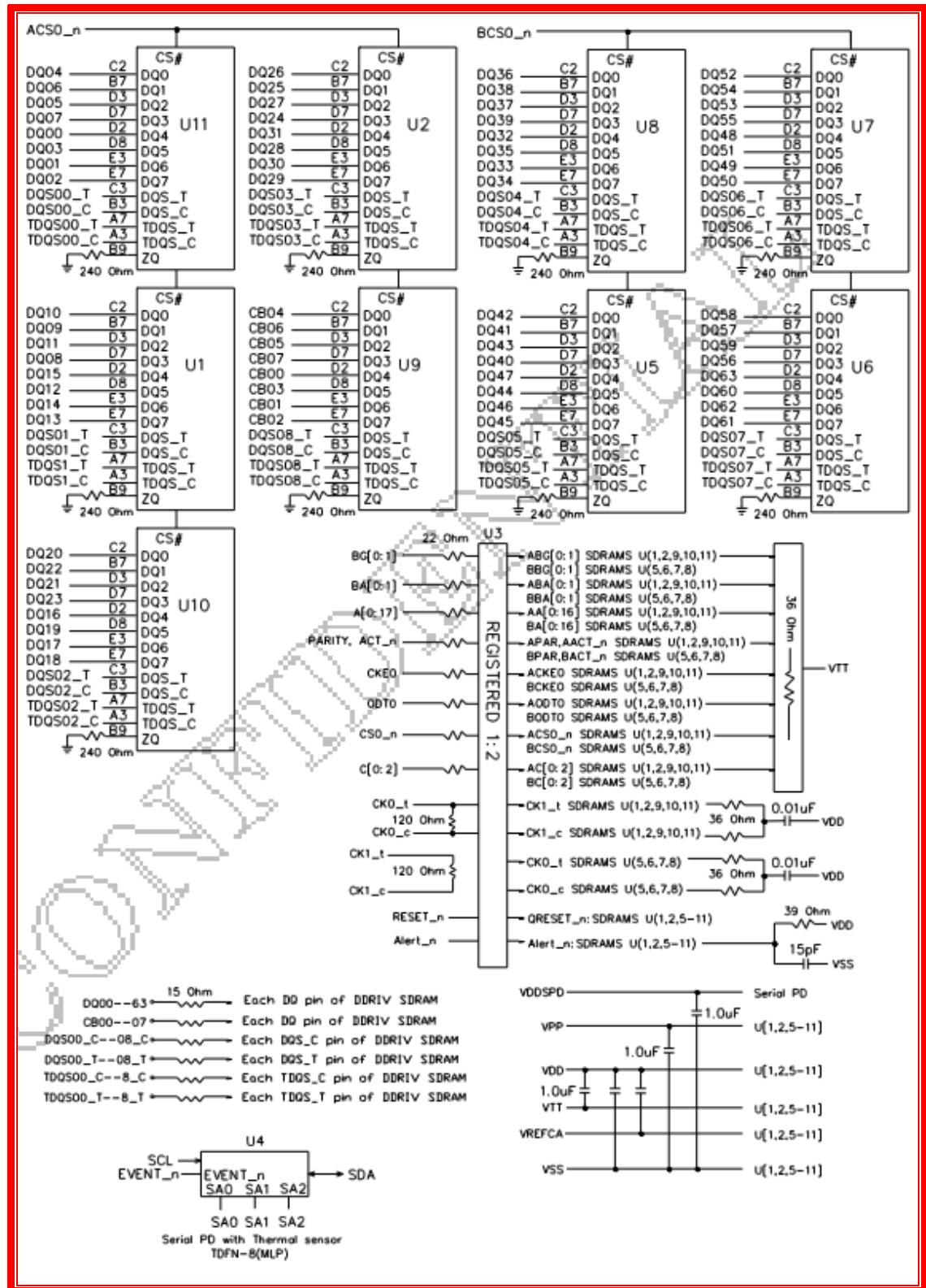
4. Architecture

Pin Definition

| Pin Name | Description | Pin Name | Description |
|--|--|------------------------------------|--|
| A0–A17 ¹ | Register address input | SCL | I ² C serial bus clock for SPD/TSE and register |
| BA0, BA1 | Register bank select input | SDA | I ² C serial bus data line for SPD/TSE and register |
| BG0, BG1 | Register bank group select input | SA0–SA2 | I ² C slave address select for SPD/TSE and register |
| RAS _n ² | Register row address strobe input | PAR | Register parity input |
| CAS _n ³ | Register column address strobe input | VDD | SDRAM core power supply |
| WE _n ⁴ | Register write enable input | C0, C1,C2 | Chip ID lines for SDRAMs |
| CS0 _n , CS1 _n CS2 _n , CS3 _n | DIMM Rank Select Lines input | 12 V | Optional power Supply on socket but not used on RDIMM |
| CKE0, CKE1 | Register clock enable lines input | VREFCA | SDRAM command/address reference supply |
| ODT0, ODT1 | Register on-die termination control lines input | VSS | Power supply return (ground) |
| ACT _n | Register input for activate input | VDDSPD | Serial SPD-TSE positive power supply |
| DQ0–DQ63 | DIMM memory data bus | ALERT _n | Register ALERT _n output |
| CB0–CB7 | DIMM ECC check bits | VPP | SDRAM Supply |
| TDQS0 _t –TDQS17 _t TDQS0 _c –TDQS17 _c | Dummy loads for mixed populations of x4 based and x8 based RDIMMs. | | |
| DQS0 _t –DQS17 _t | Data Buffer data strobes (positive line of differential pair) | DM0 _n –DM8 _n | Data Mask |
| DQS0 _c –DQS17 _c | Data Buffer data strobes (negative line of differential pair) | RESET _n | Set Register and SDRAMs to a Known State |
| DBIO _n –DBI8 _n | Data Bus Inversion | EVENT _n | SPD signals a thermal event has occurred. |
| CK0 _t , CK1 _t | Register clock input (positive line of differential pair) | VTT | SDRAM I/O termination supply |
| CK0 _c , CK1 _c | Register clocks input (negative line of differential pair) | RFU | Reserved for future use |

Note 1 Address A17 is only valid for 16 Gb x4 based SDRAMs.
Note 2 RAS_n is a multiplexed function with A16.
Note 3 CAS_n is a multiplexed function with A15.
Note 4 WE_n is a multiplexed function with A14.

5. Function Block Diagram:
 - (8GB, 1 Rank 1Gx8 DDR4 SDRAMs)



Note: 1. The ZQ ball on each DDR4 component is connected to an external 240Ω ±1% resistor that is tied to ground. It is used for the calibration of the component's ODT and output driver.

6. SDRAM Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units | Note | |
|------------------------------------|--|-----------------|-----------|------|-----|
| T _{OPER} | Operation Temperature | Operating Temp. | -40 to 85 | °C | 1,2 |
| | | Extended Temp. | 85 to 95 | °C | 1,3 |
| T _{STG} | Storage Temperature | -55 to 100 | °C | 4,5 | |
| V _{IN} , V _{OUT} | Voltage on any pins relative to V _{SS} | -0.3 to +1.5 | V | 4 | |
| V _{DD} | Voltage on VDD supply relative to V _{SS} | -0.3 to +1.5 | V | 4,6 | |
| V _{DDQ} | Voltage on VDDQ supply relative to V _{SS} | -0.3 to +1.5 | V | 4,6 | |

Note:

- 1) Operating Temperature T_{OPER} is the case surface temperature on the center/top side of the DRAM.
- 2) The Industrial Temperature Range specifies the temperatures where all DRAM specifications will be supported. During operation, the DRAM case temperature must be maintained between -40-85°C under all operating conditions.
- 3) Some applications require operation of the Extended Temperature Range between 85°C and 95°C case temperature. Full specifications are guaranteed in this range, but the following additional conditions apply:
 - a) Refresh commands must be doubled in frequency, therefore reducing the refresh interval tREFI to 3.9us.
 - b) If Self-Refresh operation is required in the Extended Temperature Range, then it is mandatory to either use the Manual Self-Refresh mode with Extended Temperature Range capability (MR2 A6 = 0b and MR2 A7 = 1b), in this case IDD6 current can be increased around 10~20% than normal Temperature range.
4. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
5. Storage Temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JESD51-2 standard.
6. VDD and VDDQ must be within 300 mV of each other at all times; and VREF must be not greater than 0.6 x VDDQ, When VDD and VDDQ are less than 500 mV; VREF may be equal to or less than 300 mV

7. Operating Condition

| Symbol | Parameter | Min | Nom | Max | Units | Notes |
|------------|---|------------|-----------|------------|-------|-------|
| VDD | Supply Voltage | 1.14 | 1.2 | 1.26 | V | 1 |
| VPP | DRAM activating power supply | 2.375 | 2.5 | 2.75 | V | 2 |
| VREFCA(DC) | Input reference voltage command/ address bus | 0.49 x VDD | 0.5 x VDD | 0.51 x VDD | V | 3 |
| VTT | Termination Voltage | 0.49 x VDD | 0.5 x VDD | 0.51 x VDD | V | 4 |

Note:

1. VDDQ tracks with VDD; VDDQ and VDD are tied together.
2. VPP must be greater than or equal to VDD at all times.
3. VREFCA must not be greater than 0.6 x VDD. When VDD is less than 500mV, VREF may be less than or equal to 300mV.
4. VTT termination voltages in excess of the specification limit adversely affect the voltage margins of command and address signals and reduce timing margins.

8. Operating, Standby, and Refresh Currents

- 8GB RDIMM (1 Rank 1Gx8 DDR4 SDRAMs)

| Symbol | Proposed Conditions | Value | | Units |
|--------|--|----------|----------|-------|
| | | IDD Max. | IPP Max. | |
| IDD0 | Operating One Bank Active-Precharge Current (AL=0)CKE: High; External clock: On; tCK, nRC, nRAS, CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n: Highbetween ACT and PRE; Command, Address, Bank Group Address, Bank Address Inputs: partially toggling; Data IO: VDDQ; DM_n:stable at 1; Bank Activity: Cycling with one bank active at a time: 0,0,1,1,2,2,... ; Output Buffer and RTT: Enabled in Mode Registers2;ODT Signal: stable at 0; Pattern Details: Refer to Component Datasheet for detail pattern | 243 | 36 | mA |
| IDD0A | Operating One Bank Active-Precharge Current (AL=CL-1) AL = CL-1, Other conditions: see IDD0 | 261 | 36 | mA |
| IDD1 | Operating One Bank Active-Read-Precharge Current (AL=0)CKE: High; External clock: On; tCK, nRC, nRAS, nRCD, CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n: Highbetween ACT, RD and PRE; Command, Address, Bank Group Address, Bank Address Inputs, Data IO: partially toggling; DM_n: stableat 1; Bank Activity: Cycling with one bank active at a time: 0,0,1,1,2,2,... ; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: stable at 0; Pattern Details: Refer to Component Datasheet for detail pattern | 288 | 36 | mA |
| IDD1A | Operating One Bank Active-Read-Precharge Current (AL=CL-1) AL = CL-1, Other conditions: see IDD1 | 306 | 36 | mA |
| IDD2N | Precharge Standby Current (AL=0)CKE: High; External clock: On; tCK, CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n: stable at 1; Command,Address, Bank Group Address, Bank Address Inputs: partially toggling ; Data IO: VDDQ; DM_n: stable at 1; Bank Activity: all banks closed; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: stable at 0; Pattern Details: Refer to Component Datasheet for detail pattern | 162 | 27 | mA |
| IDD2NA | Precharge Standby Current (AL=CL-1) AL = CL-1, Other conditions: see IDD2N | 162 | 27 | mA |

| | | | | |
|-----------|---|-----|----|----|
| IDD2NT | Precharge Standby ODT Current CKE: High; External clock: On; tCK, CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n: stable at 1; Command, Address, Bank Group Address, Bank Address Inputs: partially toggling ; Data IO: VSSQ; DM_n: stable at 1; Bank Activity: all banks closed; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: toggling according ; Pattern Details: Refer to Component Datasheet for detail pattern | 162 | 27 | mA |
| IDD2NL | Precharge Standby Current with CAL enabled Same definition like for IDD2N, CAL enabled3 | 126 | 27 | mA |
| IDD2NG | Precharge Standby Current with Gear Down mode enabled Same definition like for IDD2N, Gear Down mode enabled3 | 153 | 27 | mA |
| IDD2ND | Precharge Standby Current with DLL disabled Same definition like for IDD2N, DLL disabled3 | 153 | 27 | mA |
| IDD2N_par | Precharge Standby Current with CA parity enabled Same definition like for IDD2N, CA parity enabled3 | 171 | 27 | mA |
| IDD2P | Precharge Power-Down Current CKE: Low; External clock: On; tCK, CL: Refer to Component Datasheet for detail pattern; BL: 81; AL:0; CS_n: stable at 1; Command, Address, Bank Group Address, Bank Address Inputs: stable at 0; Data IO: VDDQ; DM_n: stable at 1; Bank Activity: all banks closed; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: stable at 0 | 99 | 27 | mA |
| IDD2Q | Precharge Quiet Standby Current CKE: High; External clock: On; tCK, CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n: stable at 1; Command, Address, Bank Group Address, Bank Address Inputs: stable at 0; Data IO: VDDQ; DM_n: stable at 1; Bank Activity: all banks closed; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: stable at 0 | 153 | 27 | mA |
| IDD3N | Active Standby Current CKE: High; External clock: On; tCK, CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n: stable at 1; Command, Address, Bank Group Address, Bank Address Inputs: partially toggling ; Data IO: VDDQ; DM_n: stable at 1; Bank Activity: all banks open; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: stable at 0; Pattern Details: Refer to Component Datasheet for detail pattern | 243 | 27 | mA |

| | | | | |
|--------|---|-----|----|----|
| IDD3NA | Active Standby Current (AL=CL-1) AL = CL-1, Other conditions: see IDD3N | 252 | 27 | mA |
| IDD3P | Active Power-Down Current CKE: Low; External clock: On; tCK, CL: sRefer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n: stable at 1; Command, Address, Bank Group Address, Bank Address Inputs: stable at 0; Data IO: VDDQ; DM_n: stable at 1; Bank Activity: all banks open; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: stable at 0 | 171 | 27 | mA |
| IDD4R | Operating Burst Read Current CKE: High; External clock: On; tCK, CL: Refer to Component Datasheet for detail pattern; BL: 82; AL: 0; CS_n: High between RD; Command, Address, Bank Group Address, Bank Address Inputs: partially toggling ; Data IO: seamless read data burst with different data between one burst and the next one according ; DM_n: stable at 1; Bank Activity: all banks open, RD commands cycling through banks: 0,0,1,1,2,2,... ; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: stable at 0; Pattern Details: Refer to Component Datasheet for detail pattern | 738 | 27 | mA |
| IDD4RA | Operating Burst Read Current (AL=CL-1) AL = CL-1, Other conditions: see IDD4R | 774 | 27 | mA |
| IDD4RB | Operating Burst Read Current with Read DBI Read DBI enabled ³ , Other conditions: see IDD4R | 765 | 27 | mA |
| IDD4W | Operating Burst Write Current CKE: High; External clock: On; tCK, CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n: High between WR; Command, Address, Bank Group Address, Bank Address Inputs: partially toggling ; Data IO: seamless write data burst with different data between one burst and the next one ; DM_n: stable at 1; Bank Activity: all banks open, WR commands cycling through banks: 0,0,1,1,2,2,... ; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: stable at HIGH; Pattern Details: Refer to Component Datasheet for detail pattern | 720 | 27 | mA |
| IDD4WA | Operating Burst Write Current (AL=CL-1) AL = CL-1, Other conditions: see IDD4W | 765 | 27 | mA |
| IDD4WB | Operating Burst Write Current with Write DBI Write DBI enabled ³ , Other conditions: see IDD4W | 720 | 27 | mA |

| | | | | |
|-----------|---|------|-----|----|
| IDD4WC | Operating Burst Write Current with Write CRC Write CRC enabled ³ , Other conditions: see IDD4W | 639 | 27 | mA |
| IDD4W_par | Operating Burst Write Current with CA Parity CA Parity enabled ³ , Other conditions: see IDD4W | 801 | 27 | mA |
| IDD5B | Burst Refresh Current (1X REF) CKE: High; External clock: On; tCK, CL, nRFC: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n: High between REF; Command, Address, Bank Group Address, Bank Address Inputs: partially toggling ; Data IO: VDDQ; DM_n: stable at 1; Bank Activity: REF command every nRFC ; Output Buffer and RTT: Enabled in Mode Registers ² ; ODT Signal: stable at 0; Pattern Details: Refer to Component Datasheet for detail pattern | 1665 | 162 | mA |
| IDD5F2 | Burst Refresh Current (2X REF) tRFC=tRFC_x2, Other conditions: see IDD5B | 1170 | 135 | mA |
| IDD5F4 | Burst Refresh Current (4X REF) tRFC=tRFC_x4, Other conditions: see IDD5B | 972 | 126 | mA |
| IDD6N | Self Refresh Current: Normal Temperature Range TCASE: 0 - 85°C; Low Power Array Self Refresh (LP ASR) : Normal ⁴ ; CKE: Low; External clock: Off; CK_t and CK_c#: LOW; CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n#, Command, Address, Bank Group Address, Bank Address, Data IO: High; DM_n: stable at 1; Bank Activity: Self-Refresh operation; Output Buffer and RTT: Enabled in Mode Registers ² ; ODT Signal: MIDDLELEVEL | 189 | 36 | mA |
| IDD6E | Self-Refresh Current: Extended Temperature Range) TCASE: 0 - 95°C; Low Power Array Self Refresh (LP ASR) : Extended ⁴ ; CKE: Low; External clock: Off; CK_t and CK_c: LOW; CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n, Command, Address, Bank Group Address, Bank Address, Data IO: High; DM_n:stable at 1; Bank Activity: Extended Temperature Self-Refresh operation; Output Buffer and RTT: Enabled in Mode Registers ² ; ODT Signal: MID-LEVEL | 306 | 45 | mA |

| | | | | |
|--------|---|------|----|----|
| IDDD6R | <p>Self-Refresh Current: Reduced Temperature Range</p> <p>TCASE: 0 - TBD (~35-45)°C; Low Power Array Self Refresh (LP ASR) : Reduced4; CKE: Low; External clock: Off; CK_t and CK_c#: LOW;</p> <p>CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n#, Command, Address, Bank Group Address, Bank Address, Data IO: High; DM_n:stable at 1; Bank Activity: Extended Temperature Self-Refresh operation; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: MID-LEVEL</p> | 135 | 45 | mA |
| IDDD6A | <p>Auto Self-Refresh Current</p> <p>TCASE: 0 - 95°C; Low Power Array Self Refresh (LP ASR) : Auto4;Partial Array Self-Refresh (PASR): Full Array; CKE: Low; External clock: Off; CK_t and CK_c#: LOW; CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: 0; CS_n#, Command, Address, Bank Group Address, Bank Address, Data IO: High; DM_n:stable at 1; Bank Activity: Auto Self-Refresh operation; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: MID-LEVEL</p> | 189 | 45 | mA |
| IDDD7 | <p>Operating Bank Interleave Read Current</p> <p>CKE: High; External clock: On; tCK, nRC, nRAS, nRCD, nRRD, nFAW, CL: Refer to Component Datasheet for detail pattern; BL: 81; AL: CL-1; CS_n: High between ACT and RDA; Command, Address, Bank Group Address, Bank Address Inputs: partially toggling ; DataIO: read data bursts with different data between one burst and the next one ; DM_n: stable at 1; Bank Activity: two times interleaved cycling through banks (0, 1, ...7) with different addressing; Output Buffer and RTT: Enabled in Mode Registers2; ODT Signal: stable at 0; Pattern Details: Refer to Component Datasheet for detail pattern</p> | 1215 | 90 | mA |
| IDDD8 | Maximum Power Down Current TBD | 81 | 27 | mA |

9. Timing Parameters

| Clock Timing | | | | |
|---|-----------------|---|---|----------|
| Parameter | Symbol | MIN | MAX | Units |
| Minimum Clock Cycle Time (DLL off mode) | tCK (DLL_OFF) | 8 | 20 | ns |
| Average Clock Period | tCK(avg) | 0.833 | <0.938 | ns |
| Average high pulse width | tCH(avg) | 0.48 | 0.52 | tCK(avg) |
| Average low pulse width | tCL(avg) | 0.48 | 0.52 | tCK(avg) |
| Absolute Clock Period | tCK(abs) | tCK(avg)min + tJIT(per)min_ to t | tCK(avg)m ax + tJIT(per)m ax_tot | tCK(avg) |
| Absolute clock HIGH pulse width | tCH(abs) | 0.45 | - | tCK(avg) |
| Absolute clock LOW pulse width | tCL(abs) | 0.45 | - | tCK(avg) |
| Clock Period Jitter- total | JIT(per)_tot | -42 | 42 | ps |
| Clock Period Jitter- deterministic | JIT(per)_dj | -21 | 21 | ps |
| Clock Period Jitter during DLL locking period | tJIT(per, lck) | -33 | 33 | ps |
| Cycle to Cycle Period Jitter | tJIT(cc)_to-tal | 83 | | ps |
| Cycle to Cycle Period Jitter deter-ministic | tJIT(cc)_dj | 42 | | ps |
| Cycle to Cycle Period Jitter during DLL locking period | tJIT(cc, lck) | 67 | | ps |
| Cumulative error across 2 cycles | tERR(2per) | -61 | 61 | ps |
| Cumulative error across 3 cycles | tERR(3per) | -73 | 73 | ps |
| Cumulative error across 4 cycles | tERR(4per) | -81 | 81 | ps |
| Cumulative error across 5 cycles | tERR(5per) | -87 | 87 | ps |
| Cumulative error across 6 cycles | tERR(6per) | -92 | 92 | ps |

| | | | | |
|---|-------------|--|-----|----|
| Cumulative error across 7 cycles | tERR(7per) | -97 | 97 | ps |
| Cumulative error across 8 cycles | tERR(8per) | -101 | 101 | ps |
| Cumulative error across 9 cycles | tERR(9per) | -104 | 104 | ps |
| Cumulative error across 10 cycles | tERR(10per) | -107 | 107 | ps |
| Cumulative error across 11 cycles | tERR(11per) | -110 | 110 | ps |
| Cumulative error across 12 cycles | tERR(12per) | -112 | 112 | ps |
| Cumulative error across 13 cycles | tERR(13per) | -114 | 114 | ps |
| Cumulative error across 14 cycles | tERR(14per) | -116 | 116 | ps |
| Cumulative error across 15 cycles | tERR(15per) | -118 | 118 | ps |
| Cumulative error across 16 cycles | tERR(16per) | -120 | 120 | ps |
| Cumulative error across 17 cycles | tERR(17per) | -122 | 122 | ps |
| Cumulative error across 18 cycles | tERR(18per) | -124 | 124 | ps |
| Cumulative error across n = 13, 14 . . . 49, 50 cycles | tERR(nper) | $tERR(nper)_{min} = ((1 + 0.68\ln(n)) * tJIT(per)_{total\ min})$ $tERR(nper)_{max} = ((1 + 0.68\ln(n)) * tJIT(per)_{total\ max})$ | | ps |
| Command and Address setup time to CK_t, CK_c referenced to Vih(ac) / Vil(ac) levels | tIS(base) | 62 | - | ps |
| Command and Address setup time to CK_t, CK_c referenced to Vref levels | tIS(Vref) | 162 | - | ps |
| Command and Address hold time to CK_t, CK_c referenced to Vih(dc) / Vil(dc) levels | tIH(base) | 87 | - | ps |

| | | | | |
|--|--------------|------------------|-----|-------|
| Command and Address hold time to CK_t, CK_c referenced to Vref levels | tIH(Vref) | 162 | - | ps |
| Control and Address Input pulse width for each input | tIPW | 410 | - | ps |
| Command and Address Timing | | | | |
| Parameter | Symbol | MIN | MAX | Units |
| CAS_n to CAS_n command delay for same bank group | tCCD_L | max(5 nCK, 5 ns) | - | nCK |
| CAS_n to CAS_n command delay for different bank group | tCCD_S | 4 | - | nCK |
| ACTIVATE to ACTIVATE Command delay to different bank group for 2KB page size | tRRD_S(2K) | Max(4nCK, 5.3ns) | - | nCK |
| ACTIVATE to ACTIVATE Command delay to different bank group for 1KB page size | tRRD_S(1K) | Max(4nCK, 3.3ns) | - | nCK |
| ACTIVATE to ACTIVATE Command delay to different bank group for 1/2KB page size | tRRD_S(1/2K) | Max(4nCK, 3.3ns) | - | nCK |
| ACTIVATE to ACTIVATE Command delay to same bank group for 2KB page size | tRRD_L(2K) | Max(4nCK, 6.4ns) | - | nCK |
| ACTIVATE to ACTIVATE Command delay to same bank group for 1KB page size | tRRD_L(1K) | Max(4nCK, 4.9ns) | - | nCK |
| ACTIVATE to ACTIVATE Command delay to same bank group for 1/2KB page size | tRRD_L(1/2K) | Max(4nCK, 4.9ns) | - | nCK |
| Four activate window for 2KB page size | tFAW_2K | Max(28nCK, 30ns) | - | ns |
| Four activate window for 1KB page size | tFAW_1K | Max(20nCK, 21ns) | - | ns |
| Four activate window for 1/2KB page size | tFAW_1/2K | Max(16nCK, 13ns) | - | ns |
| Delay from start of internal | tWTR_S | max(2nCK, 2.1ns) | - | |

| | | | | |
|--|---------------|---|---|-----|
| write transaction to internal read com-mand for different bank group | | 5ns) | | |
| Delay from start of internal write transaction to internal read com-mand for same bank group | tWTR_L | max(4nCK,7.5ns) | - | |
| Internal READ Command to PRE-CHARGE Command delay | tRTP | max(4nCK,7.5ns) | - | |
| WRITE recovery time | tWR | 15 | - | ns |
| Write recovery time when CRC and DM are enabled | tWR_CRC_DM | tWR+max(5nCK,3.75ns) | - | ns |
| delay from start of internal write transaction to internal read com-mand for different bank group with both CRC and DM enabled | tWTR_S_CRC_DM | tWTR_S+max(5nCK,3.75ns) | - | ns |
| delay from start of internal write transaction to internal read com-mand for same bank group with both CRC and DM enabled | tWTR_L_CRC_DM | tWTR_L+max(5nCK,3.75ns) | - | ns |
| DLL locking time | tDLLK | 768 | - | nCK |
| Mode Register Set command cycle time | tMRD | 8 | - | nCK |
| Mode Register Set command up-date delay | tMOD | max(24nCK,15ns) | - | |
| Multi-Purpose Register Recovery Time | tMPRR | 1 | - | nCK |
| Multi Purpose Register Write Re-covey Time | tWR_MPR | tMOD (min) + AL + PL | - | - |
| Auto precharge write recovery + precharge time | tDAL(min) | Programmed WR + roundup (tRP / tCK(avg)) | | nCK |
| DQ0 or DQL0 driven to 0 set-up time to first DQS rising edge | tPDA_S | 0.5 | - | UI |

| | | | | |
|--|----------|------|------|----------------|
| DQ0 or DQ10 driven to 0 hold time from last DQS falling edge | tPDA_H | 0.5 | - | UI |
| CS_n to Command Address Latency | | | | |
| CS_n to Command Address Latency | tCAL | 5 | - | nCK |
| DRAM Data Timing | | | | |
| DQS_t,DQS_c to DQ skew, per group, per access | tDQSQ | - | 0.16 | tCK(avg) /2 |
| DQ output hold time from DQS_t,DQS_c | tQH | 0.78 | - | tCK(avg) /2 |
| Data Valid Window per device: tQH – tDQSQ for a device | tDVWd | 0.64 | - | UI |
| Data Valid Window per device, per pin: tQH – tDQSQ each device's out-put | tDVWp | 0.72 | - | UI |
| Data Strobe Timing | | | | |
| DQS_t, DQS_c differential READ Preamble | tRPRE | 0.9 | | tCK |
| DQS_t, DQS_c differential READ Postamble | tRPST | 0.33 | TBD | tCK |
| DQS_t,DQS_c differential output high time | tQSH | 0.4 | - | tCK |
| DQS_t,DQS_c differential output low time | tQSL | 0.4 | - | tCK |
| DQS_t, DQS_c differential WRITE Preamble | tWPRE | 0.9 | - | tCK |
| DQS_t, DQS_c differential WRITE Postamble | tWPST | 0.33 | TBD | tCK |
| DQS_t and DQS_c low-impedance time (Referenced from RL-1) | tLZ(DQS) | -300 | 150 | ps |
| DQS_t and DQS_c high-impedance time (Referenced from RL+BL/2) | tHZ(DQS) | - | 150 | ps |
| DQS_t, DQS_c differential | tDQSL | 0.46 | 0.54 | tCK |

| | | | | |
|---|-----------------|----------------------------|------|-----|
| input low pulse width | | | | |
| DQS_t, DQS_c differential input high pulse width | tDQSH | 0.46 | 0.54 | tCK |
| DQS_t, DQS_c rising edge to CK_t, CK_c rising edge (1 clock preamble) | tDQSS | -0.27 | 0.27 | tCK |
| DQS_t, DQS_c falling edge setup time to CK_t, CK_c rising edge | tDSS | 0.18 | - | tCK |
| DQS_t, DQS_c falling edge hold time from CK_t, CK_c rising edge | tDSH | 0.18 | - | tCK |
| DQS_t, DQS_c rising edge output timing ocaation from rising | tDQSK (DLL On) | -175 | 175 | ps |
| DQS_t, DQS_c rising edge output variance window per DRAM | tDQSKI (DLL On) | | 290 | ps |
| MPSM Timing | | | | |
| Command path disable delay upon MPSM entry | tMPED | tMOD(min) + tCPDED(min) | - | |
| Valid clock requirement after MPSM entry | tCKMPE | tMOD(min) + tCPDED(min) | - | |
| Valid clock requirement before MPSM exit | tCKMPX | tCKSRX(min) | | |
| Exit MPSM to commands not requiring a locked DLL | tXMP | txs(imin) | | |
| Exit MPSM to commands requiring a locked DLL | tXMPDLL | tXMP(min) + tXSDLL(min) | | |
| CS setup time to CKE | tMPX_S | tISmin + tIHmin | - | |
| Calibration Timing | | | | |
| Power-up and RESET calibration time | tZQinit | 1024 | - | nCK |
| Normal operation Full calibration time | tZQoper | 512 | - | nCK |
| Normal operation Short | tZQCS | 128 | - | nCK |

| | | | | |
|---|------------------|-----------------------------------|---|--|
| calibration time | | | | |
| Reset/Self Refresh Timing | | | | |
| Exit Reset from CKE HIGH to a valid command | command tXPR | max (5nCK,tRFC(min))+ 10ns) | - | |
| Exit Self Refresh to commands not requiring a locked DLL | tXS | tRFC(min)+1 0ns | - | |
| SRX to commands not requiring a locked DLL in Self Refresh ABORT | tX-S_ABORT(min) | tRFC4(min)+ 10ns | - | |
| Exit Self Refresh to ZQCL,ZQCS and MRS (CL,CWL,WR,RTP and Gear Down) | tXS_FAST (min) | tRFC4(min)+ 10ns | - | |
| Exit Self Refresh to commands re-quiring a locked DLL | tXSDLL | tDLLK(min) | - | |
| Minimum CKE low width for Self re-fresh entry to exit timing | tCKESR | tCKE(min)+1 nCK | - | |
| Minimum CKE low width for Self re-fresh entry to exit timing with CA Parity enabled | tCKESR_PAR | tCKE(min)+ 1nCK+PL | - | |
| Valid Clock Requirement after Self Refresh Entry (SRE) or Power- Down Entry (PDE) | tCKSRE | max(5nCK,10 ns) | - | |
| Valid Clock Requirement after Self Refresh Entry (SRE) or Power- Down when CA Parity is enabled | tCKS-RE_PAR | max (5nCK,10ns) +PL | - | |
| Valid Clock Requirement before Self Refresh Exit (SRX) or Power-Down Exit (PDX) or Reset Exit | tCKSRX | max(5nCK,10 ns) | - | |
| Power Down Timing | | | | |
| Exit Power Down with DLL on to any valid command;Exit Precharge Power Down with | tXP | (4nCK,6ns) | - | |

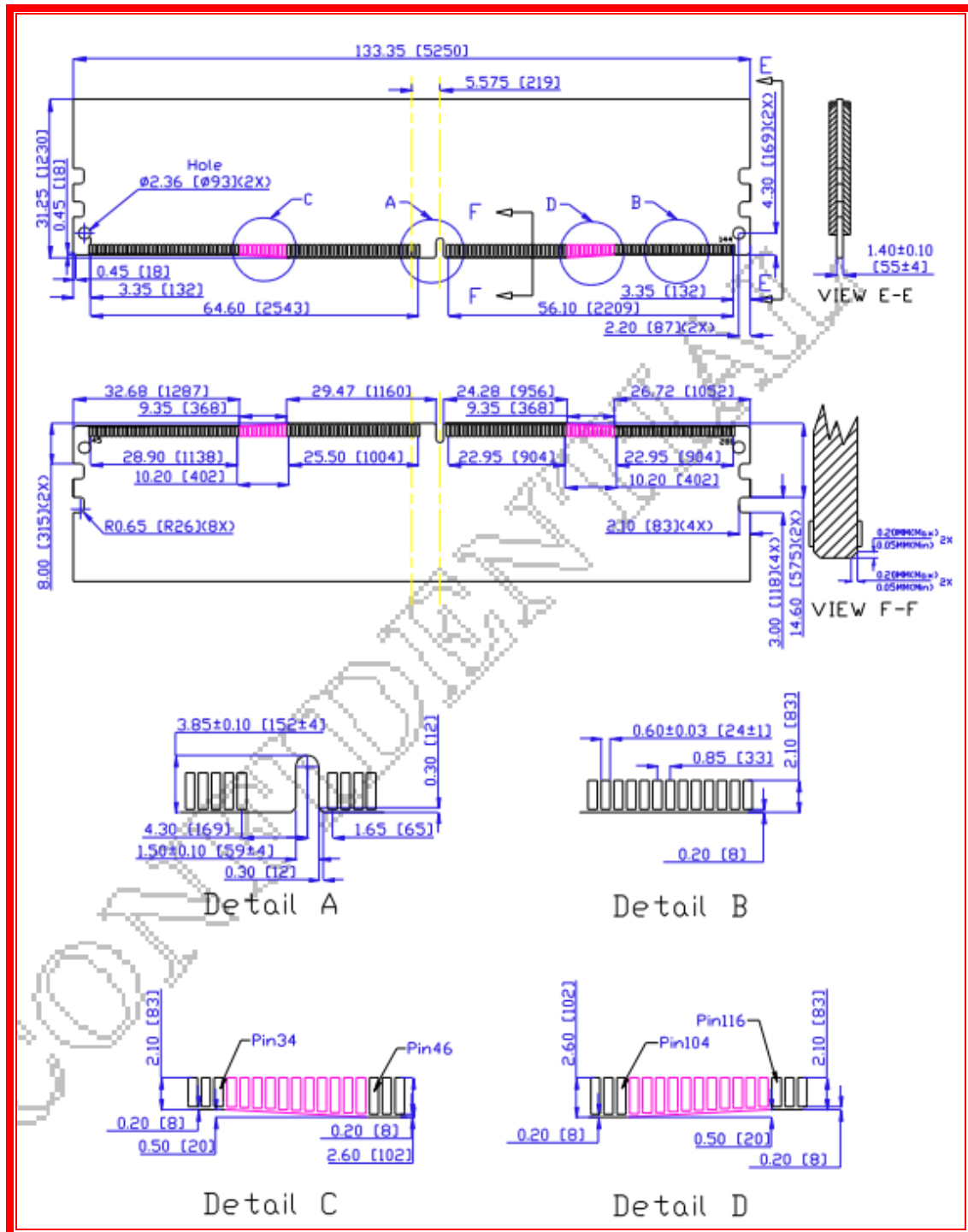
| | | | | |
|--|--------------|---------------------|---------|-----|
| DLL frozen to commands not requiring a locked DLL | | | | |
| CKE minimum pulse width | tCKE | max (3nCK, 5ns) | - | |
| Command pass disable delay | tCPDED | 4 | - | nCK |
| Power Down Entry to Exit Timing | tPD | tCKE(min) | 9*tREFI | |
| Timing of ACT command to Power Down entry | tACTPDEN | 2 | - | nCK |
| Timing of PRE or PREA command to Power Down entry | tPRPDEN | 2 | - | nCK |
| Timing of RD/RDA command to Power Down entry | tRDPDEN | RL+4+1 | - | nCK |
| Timing of WR command to Power Down entry (BL8OTF, BL8MRS, BC4OTF) | tWRPDEN | WL+4+(tWR/tCK(avg)) | - | nCK |
| Timing of WRA command to Power Down entry (BL8OTF, BL8MRS, BC4OTF) | tWRAPDEN | WL+4+WR+1 | - | nCK |
| Timing of WR command to Power Down entry (BC4MRS) | tWRP-BC4DEN | WL+2+(tWR/tCK(avg)) | - | nCK |
| Timing of WRA command to Power Down entry (BC4MRS) | tWRAP-BC4DEN | WL+2+WR+1 | - | nCK |
| Timing of REF command to Power Down entry | tREFPDEN | 2 | - | nCK |
| Timing of MRS command to Power Down entry | tMRSPDEN | tMOD(min) | - | |
| PDA Timing | | | | |
| Mode Register Set command cycle time in PDA mode | tMRD_PDA | max(16nCK, 10ns) | | |
| Mode Register Set command up-date delay in PDA mode | tMOD_PDA | tMOD | | |
| ODT Timing | | | | |
| Asynchronous RTT turn-on delay (Power-Down with DLL frozen) | tAONAS | 1.0 | 9.0 | ns |

| | | | | |
|--|----------------|------|--------|----------|
| Asynchronous RTT turn-off delay (Power-Down with DLL frozen) | tAOFAS | 1.0 | 9.0 | ns |
| RTT dynamic change skew | tADC | 0.3 | 0.7 | tCK(avg) |
| Write Leveling Timing | | | | |
| First DQS _t /DQS _n rising edge after write leveling mode is programmed | tWLMRD | 40 | - | nCK |
| DQS _t /DQS _n delay after write leveling mode is programmed | tWLDQSEN | 25 | - | nCK |
| Write leveling setup time from rising CK _t , CK _c crossing to rising DQS _t /DQS _n crossing | tWLS | 0.13 | - | tCK(avg) |
| Write leveling hold time from rising DQS _t /DQS _n crossing to rising CK _t , CK _c crossing | tWLH | 0.13 | - | tCK(avg) |
| Write leveling output delay | tWLO | 0 | 9.5 | ns |
| Write leveling output error | tWLOE | | | ns |
| CA Parity Timing | | | | |
| Commands not guaranteed to be executed during this time | tPAR_UN-KNOWN | - | PL | |
| Delay from errant command to ALERT _n assertion | tPAR_ALERT_ON | - | PL+6ns | |
| Pulse width of ALERT _n signal when asserted | tPAR_ALERT_PW | 72 | 144 | nCK |
| Time from when Alert is asserted till controller must start providing DES commands in Persistent CA parity mode | tPAR_ALERT_RSP | - | 64 | nCK |
| Parity Latency | PL | 5 | | nCK |
| CRC Error Reporting | | | | |
| CRC error to ALERT _n latency | tCRC_ALERT | 3 | 13 | ns |
| CRC ALERT _n pulse width | CRC_ALERT_PW | 6 | 10 | nCK |
| tREFI | | | | |

| | | | | |
|-------------|------|-----|---|----|
| tRFC1 (min) | 2Gb | 160 | - | ns |
| | 4Gb | 260 | - | ns |
| | 8Gb | 350 | - | ns |
| | 16Gb | 550 | - | ns |
| tRFC2 (min) | 2Gb | 110 | - | ns |
| | 4Gb | 160 | - | ns |
| | 8Gb | 260 | - | ns |
| | 16Gb | 350 | - | ns |
| tRFC3 (min) | 2Gb | 90 | - | ns |
| | 4Gb | 110 | - | ns |
| | 8Gb | 160 | - | ns |
| | 16Gb | 260 | - | ns |

10. PACKAGE DIMENSION

- (8GB, 1 Rank 1Gx8 DDR4 base RDIMM)



Note: All dimensions are in millimeters (mils) and should be kept within a tolerance of ±0.15 (6), unless otherwise specified.

11. RoHS Declaration

innodisk

宜鼎國際股份有限公司
Innodisk Corporation

Tel:(02)7703-3000 Fax:(02) 7703-3555 Internet: http://www.innodisk.com/

RoHS 自我宣告書 (RoHS Declaration of Conformity)

Manufacturer Product: All Innodisk EM Flash and Dram products

- 一、宜鼎國際股份有限公司（以下稱本公司）特此保證售予貴公司之所有產品，皆符合歐盟 2011/65/EU 及 (EU) 2015/863 關於 RoHS 之規範要求。
Innodisk Corporation declares that all products sold to the company, are complied with European Union RoHS Directive (2011/65/EU) and (EU) 2015/863 requirement.
- 二、本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。
Innodisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.
- 三、本公司聲明我們的產品符合 RoHS 指令的附件中 (7a)、(7c-1) 允許豁免。
We declare, our products permitted by the following exemptions specified in the Annex of the RoHS directive.
- ※ (7a) Lead in high melting temperature type solders (i.e. lead-based alloys containing 85% by weight or more lead).
- ※ (7C-1) Electrical and electronic components containing lead in a glass or ceramic other than dielectric ceramic in capacitors, e.g. piezoelectric devices, or in a glass or ceramic matrix compound.

| Name of hazardous substance | Limited of RoHS ppm (mg/kg) |
|-----------------------------|-----------------------------|
| 鉛 (Pb) | < 1000 ppm |
| 汞 (Hg) | < 1000 ppm |
| 鎘 (Cd) | < 100 ppm |
| 六價鉻 (Cr 6+) | < 1000 ppm |
| 多溴聯苯 (PBBs) | < 1000 ppm |
| 多溴二苯醚 (PBDEs) | < 1000 ppm |
| 鄰苯二甲酸二(2-乙基己基)酯 (DEHP) | < 1000 ppm |
| 鄰苯二甲酸丁酯苯甲酯 (BBP) | < 1000 ppm |
| 鄰苯二甲酸二丁酯 (DBP) | < 1000 ppm |
| 鄰苯二甲酸二異丁酯 (DIBP) | < 1000 ppm |

立保證書人 (Guarantor)

Company name 公司名稱：Innodisk Corporation 宜鼎國際股份有限公司

Company Representative 公司代表人：Randy Chien 簡川勝

Company Representative Title 公司代表人職稱：Chairman 董事長

Date 日期：2018 / 07 / 01



12. REACH Declaration

innodisk

宜鼎國際股份有限公司
Innodisk Corporation
REACH Declaration

Tel:(02)7703-3000 Fax:(02) 7703-3555 Internet: <http://www.innodisk.com/>

We hereby confirm that the product(s) delivered to

| Innodisk P/N | Description |
|----------------------------|-------------|
| All Innodisk DRAM Products | DDR Series |

- contain(s) **no** hazardous substances or constituents exceeding the defined threshold 0.1 % by weight in homogenous material if not otherwise specified, as described in the candidate list table currently including 201 substances and shown on the ECHA website (<http://echa.europa.eu/de/candidate-list-table>).
- contain(s) one or more hazardous substances or constituents exceeding 0.1 % by weight in homogenous material if not otherwise specified in candidate list table. Where the threshold value is exceeded, the substances in question are to be declared in accompanying Appendix A.
- Comply with REACH Annex XVII.

Guarantor

Company name 公司名稱： Innodisk Corporation 宜鼎國際股份有限公司Company Representative 公司代表人： Randy Chien 簡川勝Company Representative Title 公司代表人職稱： Chairman 董事長Date 日期： 2019 / 07 / 24

Revision Log

| Rev | Date | Modification |
|-----|--------------------------------|---------------------|
| 0.1 | 27 th November 2019 | Preliminary Edition |
| 1.0 | 27 th November 2019 | Official Released |
| 1.1 | 14 th May 2021 | Modified typo |